

Schottky Barrier Rectifier

SBL6060PT

FEATURES

- Schottky barrier chip
- Low Power Loss,High Efficiency
- Guard ring for transient protection
- High Operating Junction Temperature
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

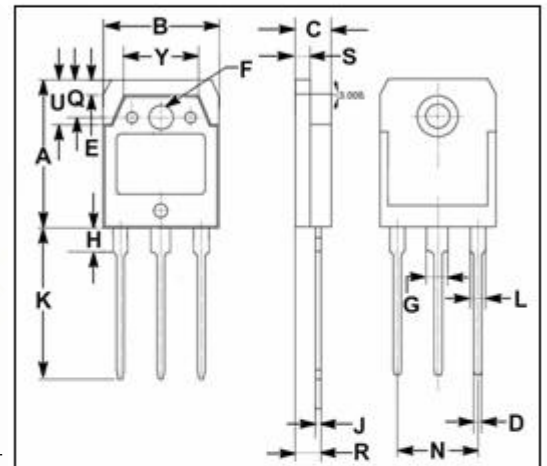
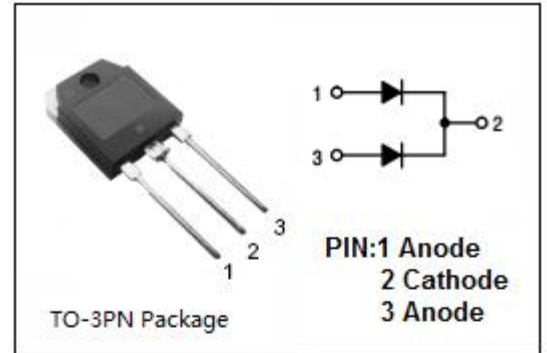
APPLICATIONS

- For use in low voltage ,high frequency inverters,free wheeling and polarity protection applications.

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ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V _{RRM} V _{RMS} V _R	Peak Repetitive Reverse Voltage RMS Voltage DC Blocking Voltage	60	V
I _{F(AV)}	Average Rectified Forward Current	60	A
I _{FSM}	Nonrepetitive Peak Surge Current 8.3ms single half sine-wave superimposed on rated load conditions	500	A
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature Range	-65~150	°C



DIM	mm	
	MIN	MAX
A	19.60	20.30
B	15.50	15.70
C	4.70	4.90
D	0.90	1.10
E	1.90	2.10
F	3.40	3.60
G	2.90	3.20
H	3.20	3.40
J	0.595	0.605
K	19.80	20.70
L	1.90	2.20
N	10.89	10.91
Q	4.90	5.10
R	3.35	3.45
S	1.995	2.100
U	5.90	6.20
Y	9.90	10.10

Schottky Barrier Rectifier**SBL6060PT****THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	0.5	$^{\circ}C/W$

ELECTRICAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	MAX	UNIT
V_F	Maximum Instantaneous Forward Voltage	$I_F = 30A ; T_j = 25^{\circ}C$	0.7	V
I_R	Maximum Instantaneous Reverse Current	$V_R = V_{RWM}; T_j = 25^{\circ}C$	20	mA
		$V_R = V_{RWM}; T_j = 100^{\circ}C$	200	mA

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